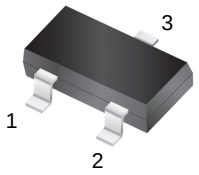
GOOD-ARK
SEMICONDUCTOR

GSBAT54xT Series
Schottky Diode

Features

- Low forward voltage drop
- Fast switching
- PN junction guard ring for transient and ESD protection



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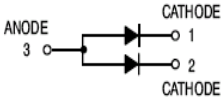
Schematic Diagram and Marking

GSBAT54T

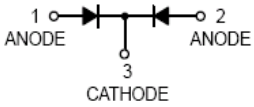
Marking: L1

GSBAT54AT



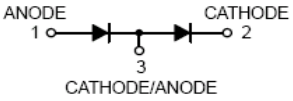
Marking: L2

GSBAT54CT



Marking: L3

GSBAT54ST



Marking: L4

Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	30	V
Working Peak Reverse Voltage	V_{RWM}	30	V
DC Reverse Voltage	V_R	30	V
Forward Continuous Voltage	I_F	200	mA
Repetitive Peak Forward Voltage	I_{FRM}	300	mA
Non-repetitive Peak Forward Surge Current @t<1.0s	I_{FSM}	600	mA
Power Dissipation	P_D	150	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	833	°C/W
Junction and Storage Temperature	T_J,T_{STG}	-65 to +150	°C

Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Max	Unit
Reverse Breakdown Voltage	$V_{(BR)R}$	I_R=100μA	30		V
Leakage Current	I_R	V_R=25V		2.0	μA
Forward Voltage	V_F	I_F=0.1mA I_F=1.0mA I_F=10mA I_F=30mA		240 320 400 500	mV
Typical Total Capacitance	C_T	V_R=1.0V,f=1MHz		10	pF
Reverse Recovery Time	t_{rr}	I_F=I_R=10mA,to I_R=1.0mA R_L=100Ω		5.0	ns

Typical Electrical Characteristic Curves

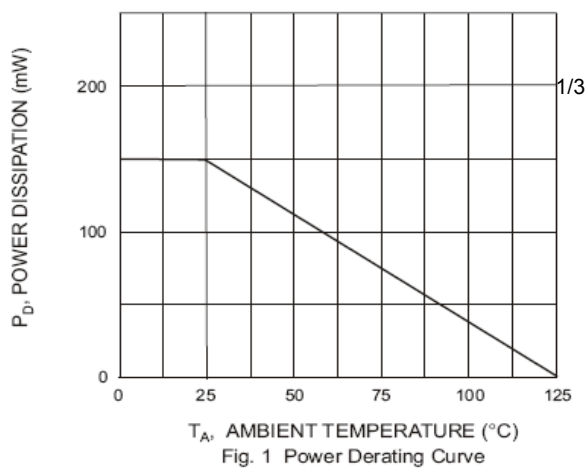


Fig. 1 Power Derating Curve

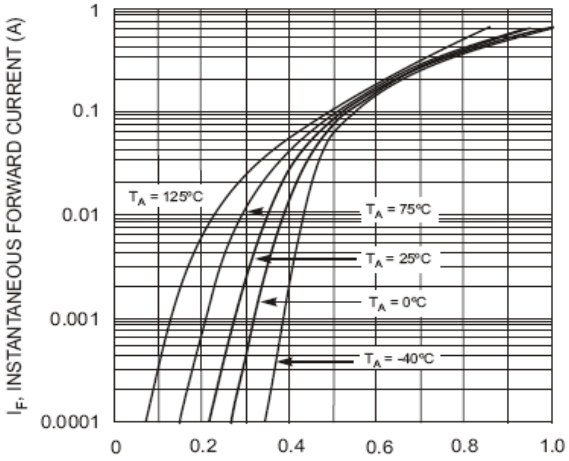


Fig. 2 Forward Characteristics

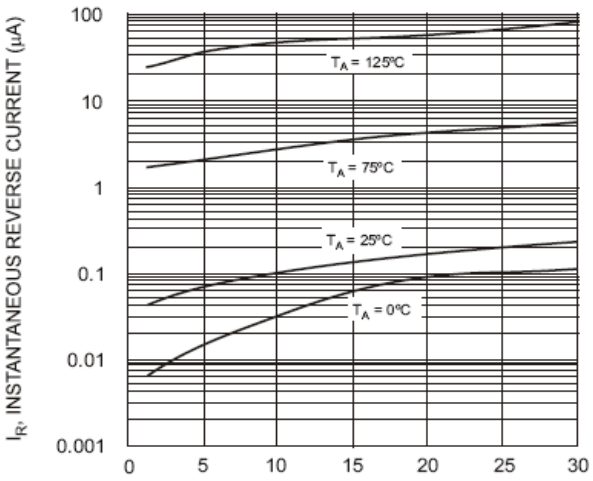


Fig. 3 Typical Reverse Characteristics

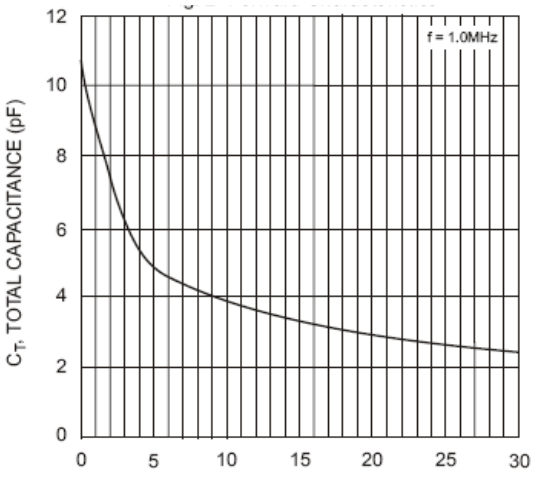


Fig. 4 Typical Capacitance vs. Reverse Voltage

Package Outline Dimensions

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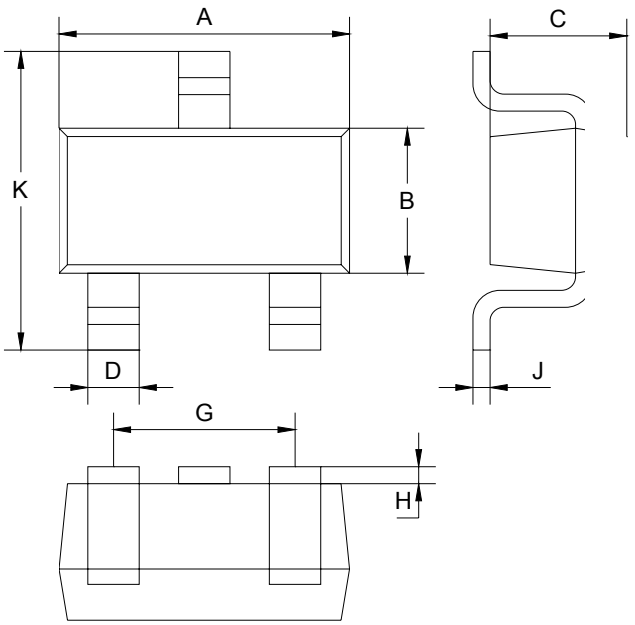

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Dim	Min	Max
A	1.5	1.7
B	0.75	0.85
C	0.6	0.8
D	0.15	0.3
G	0.9	1.1
H	0.02	0.1
J	0.1Typical	
K	1.45	1.75
All Dimensions in mm		